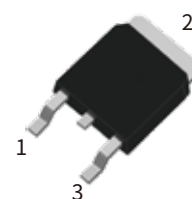


FEATURES

- | Direct interfacing to logic level ICs
- | Direct interfacing to low power gate drive circuits
- | High blocking voltage capability
- | Planar passivated for voltage ruggedness and reliability
- | Triggering in all four quadrant



TO-252

APPLICATIONS

- | General purpose motor control circuits
- | Phase control operations in light dimmers and motor speed controllers
- | Home appliances



Schematic Symbol

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600	V
RMS on-state current ($T_c=103^\circ\text{C}$)		$I_{\text{T(RMS)}}$	8	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)		I_{TSM}	65	
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	21	A^2S
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	I - II - III	di/dt	50	$\text{A}/\mu\text{s}$
	IV		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{\text{G(AV)}}$	0.5	W
Peak gate power		P_{GM}	5	W
Operating junction temperature range		T_j	-40~+125	$^\circ\text{C}$
Storage junction temperature range		T_{STG}	-40~+150	

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value				Unit
			D	E	F	G	
I_{GT}	$V_D=12\text{V}$	I - II - III	≤ 5	≤ 10	≤ 25	≤ 50	mA
		IV	≤ 10	≤ 25	≤ 70	≤ 100	
V_{GT}		ALL	≤ 1.3				V
V_{GD}	$V_D=V_{DRM}, R_L=3.3\text{K}\Omega, T_j=125^{\circ}\text{C}$		≥ 0.2				V
I_H	$I_T=100\text{mA}$		≤ 10	≤ 15	≤ 40	≤ 60	mA
I_L	$I_G=1.2I_{GT}$	I - III	≤ 10	≤ 20	≤ 50	≤ 70	
		II - IV	≤ 20	≤ 30	≤ 70	≤ 100	
dV_D/dt	$V_D=67\%V_{DRM}, T_j=125^{\circ}\text{C}$		≥ 20	≥ 50	≥ 50	≥ 200	V/ μs
V_{TM}	$I_{TM}=10\text{A}, t_p=380\mu\text{s}$		≤ 1.6				V
I_{DRM}	$V_D=V_{DRM}, V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	≤ 5				μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	≤ 1				mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case(AC)	2.1	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	Junction to ambient	70	$^{\circ}\text{C}/\text{W}$

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

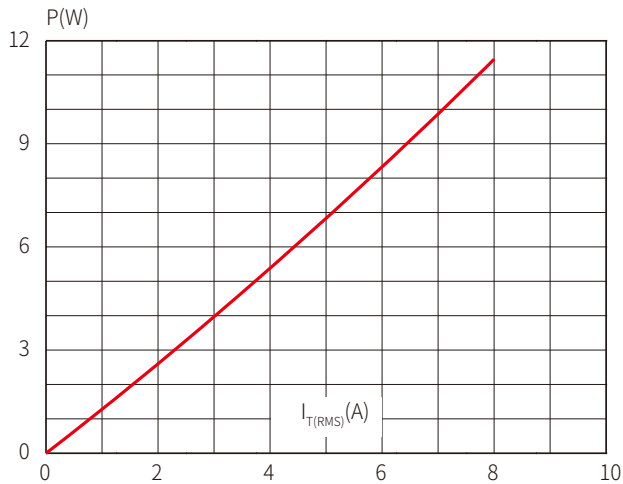


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm)(full cycle)

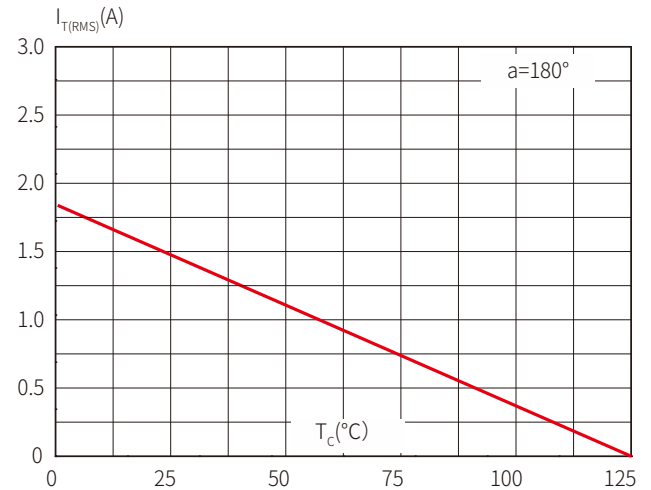


FIG.3: Surge peak on-state current versus number of cycles

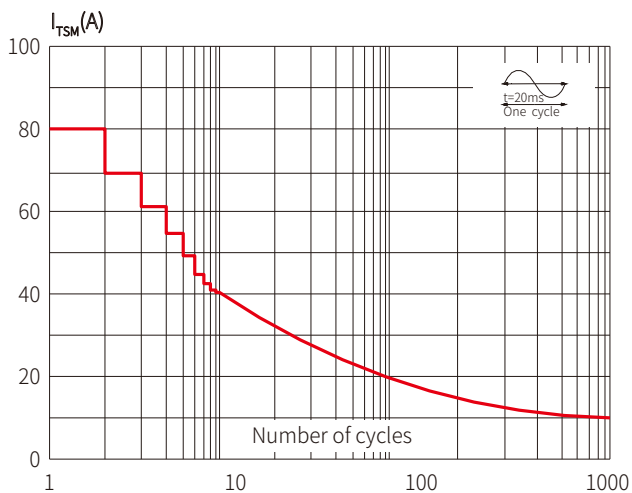


FIG.4 On-state characteristics (maximum values)

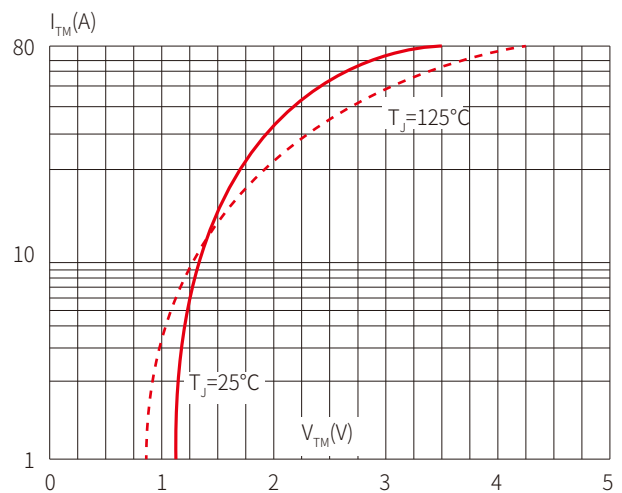


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

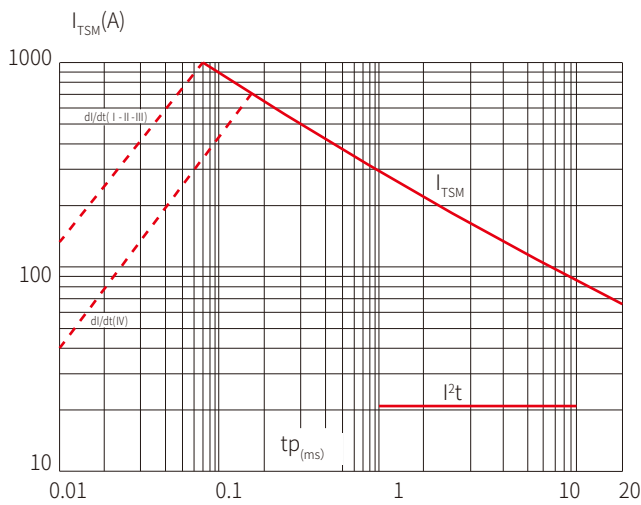


FIG.6 Relative variations of gate trigger current versus junction temperature

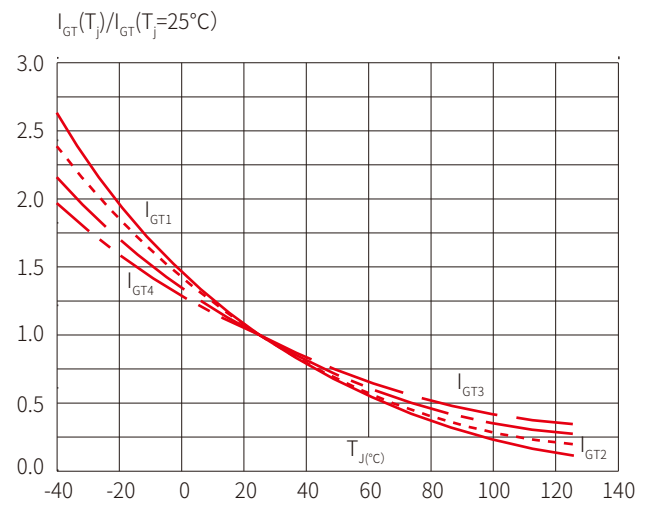


FIG.7 Relative variations of holding current versus junction temperature

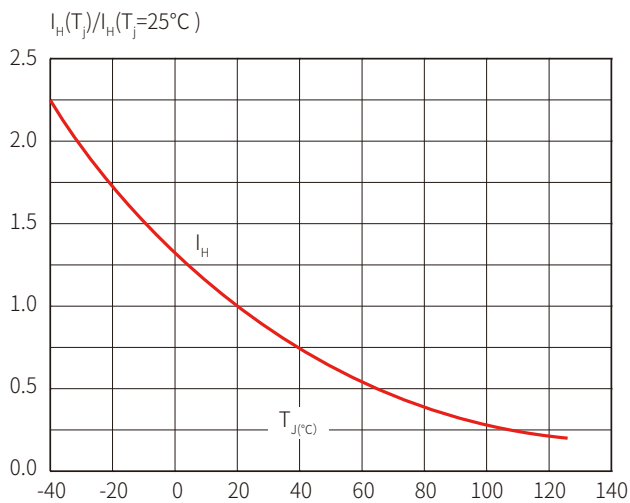
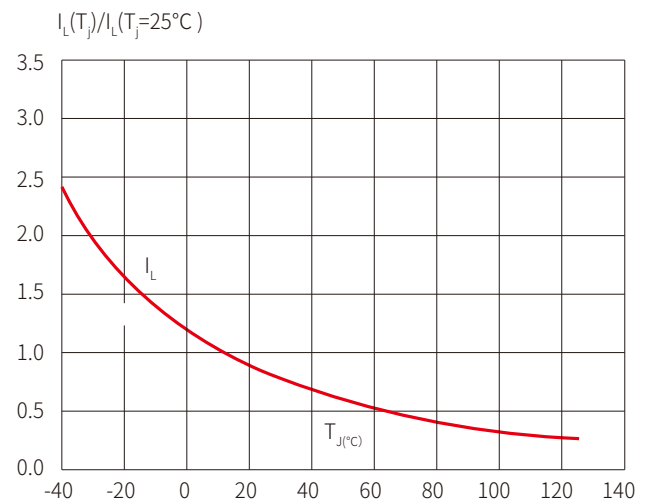
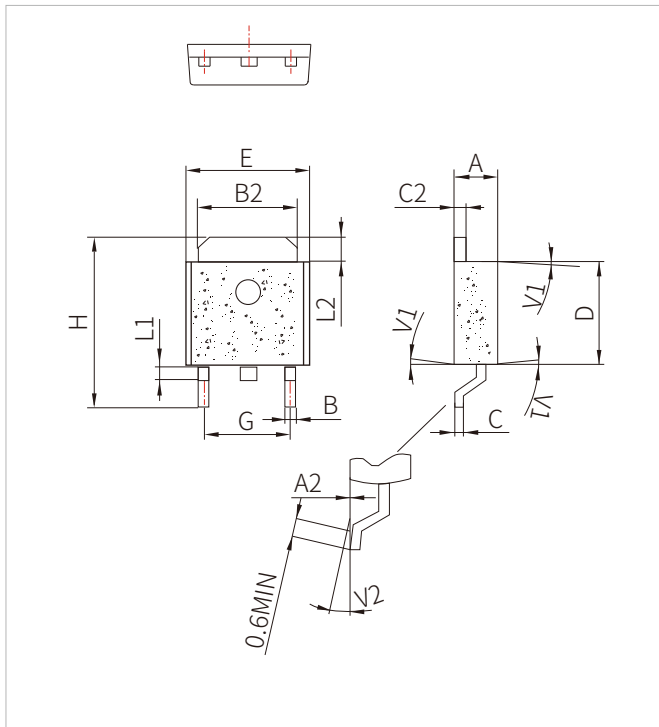


FIG.8 Relative variations of latching current versus junction temperature



TO-252 PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.80	0.252		0.268
G	4.40		4.70	0.173	0.1	0.185
H	9.35		10.7	0.368		0.421
L1	1.30		1.70	0.051	0.143	0.067
L2	1.37		1.50	0.054		0.059
V1		4°			0.130	
V2	0°		8°	0°		8°

ORDERING INFORMATION

Part Number	Package	QTY/Reel	Reel Size
STD8Q60D(E/F/G)	TO-252	2500CS	13"

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